

Excellent Integrated System Limited

Stocking Distributor

Click to view price, real time Inventory, Delivery & Lifecycle Information:

ON Semiconductor MUR2100E

For any questions, you can email us directly: <u>sales@integrated-circuit.com</u>



Distributor of ON Semiconductor: Excellent Integrated System Limited Datasheet of MUR2100E - DIODE GEN PURP 1KV 2A AXIAL Contact us: sales@integrated-circuit.com Website: www.integrated-circuit.com

MUR2100E

Preferred Device

SWITCHMODE[™] Power Rectifier Ultrafast "E" Series with High Reverse Energy Capability

These state-of-the-art devices are designed for use in switching power supplies, inverters and as free wheeling diodes.

Features

- 20 mjoules Avalanche Energy Guaranteed
- Excellent Protection Against Voltage Transients in Switching Inductive Load Circuits
- Ultrafast 75 Nanosecond Recovery Time
- 175°C Operating Junction Temperature
- Low Forward Voltage
- Low Leakage Current
- High Temperature Glass Passivated Junction
- These are Pb-Free Devices*

Mechanical Characteristics:

- Case: Epoxy, Molded
- Weight: 0.4 Gram (Approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max for 10 Seconds
- Polarity: Cathode Indicated by Polarity Band

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	1000	V
Average Rectified Forward Current (Note 1)	I _{F(AV)}	2.0 @ T _A = 35°C	A
Non-Repetitive Peak Surge Current (Surge applied at rated load conditions, halfwave, single phase, 60 Hz)	I _{FSM}	35	A
Operating Junction Temperature and Storage Temperature Range	T _J , T _{stg}	–65 to +175	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Maximum Thermal Resistance, Junction-to-Ambient	R_{\thetaJA}	(Note 3)	°C/W

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Pulse Test: Pulse Width = 300 μ s, Duty Cycle \leq 2.0%.

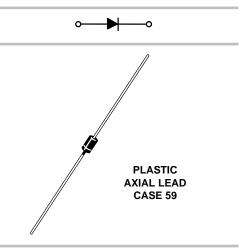
*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



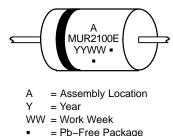
ON Semiconductor®

http://onsemi.com

ULTRAFAST RECTIFIER 2.0 AMPERES, 1000 VOLTS



MARKING DIAGRAM



(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
MUR2100E	Axial Lead**	1000 Units/Bag
MUR2100EG	Axial Lead**	1000 Units/Bag
MUR2100ERL	Axial Lead**	5000/Tape & Reel
MUR2100ERLG	Axial Lead**	5000/Tape & Reel

⁺For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

**This package is inherently Pb-Free.

Preferred devices are recommended choices for future use and best overall value.

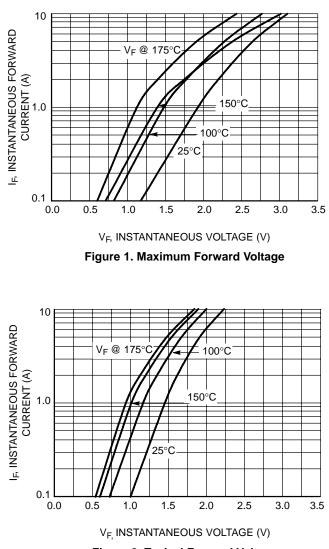


MUR2100E

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Maximum Instantaneous Forward Voltage (Note 2) ($I_F = 2.0 \text{ A}, T_J = 150^{\circ}\text{C}$) ($I_F = 2.0 \text{ A}, T_J = 25^{\circ}\text{C}$)	V _F	1.75 2.20	V
Maximum Instantaneous Reverse Current (Note 2) (Rated dc Voltage, $T_J = 100^{\circ}C$) (Rated dc Voltage, $T_J = 25^{\circ}C$)	i _R	600 10	μΑ
	t _{rr}	100 75	ns
Maximum Forward Recovery Time (I _F = 1.0 A, di/dt = 100 A/μs, I _{REC} to 1.0 V)	t _{fr}	75	ns
Controlled Avalanche Energy (See Test Circuit in Figure 6)	W _{AVAL}	10	mJ

2. Pulse Test: Pulse Width = 300 $\mu s,$ Duty Cycle \leq 2.0%.

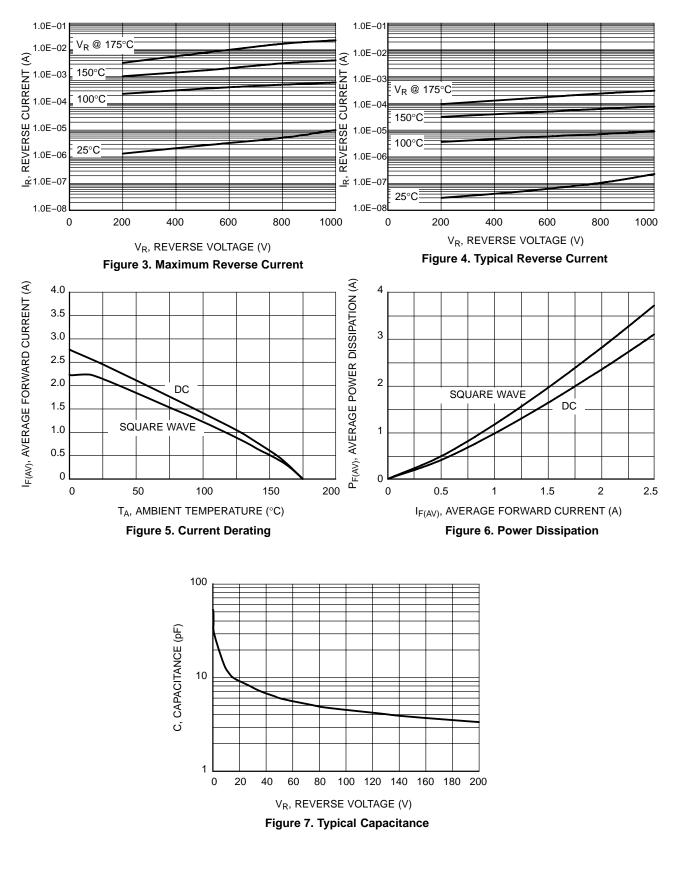






Distributor of ON Semiconductor: Excellent Integrated System Limited Datasheet of MUR2100E - DIODE GEN PURP 1KV 2A AXIAL Contact us: sales@integrated-circuit.com Website: www.integrated-circuit.com

MUR2100E





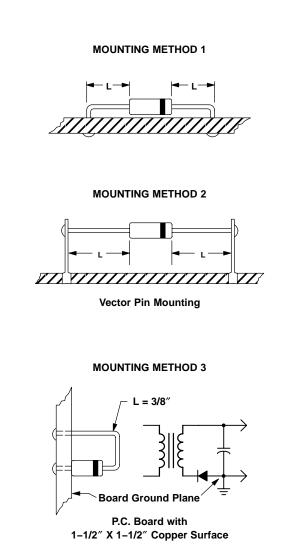
MUR2100E

NOTE 3. – AMBIENT MOUNTING DATA

Data shown for thermal resistance, junction–to–ambient $(R_{\theta JA})$ for the mountings shown is to be used as typical guideline values for preliminary engineering or in case the tie point temperature cannot be measured.

TYPICAL VALUES FOR $\textbf{R}_{\theta \textbf{JA}}$ IN STILL AIR

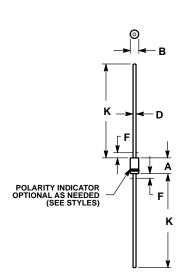
Mounti	ng	Lead Length, L			
Metho	Method		1/4	1/2	Units
1		52	65	72	°C/W
2	$R_{\theta JA}$	67	80	87	°C/W
3			50		°C/W





MUR2100E

PACKAGE DIMENSIONS



AXIAL LEAD CASE 59-10 **ISSUE U**

- NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14 5M 1982
- CONTROLLING DIMENSION: INCH
- CONTROLLING DIMENSION: INCH.
 ALL RULES AND NOTES ASSOCIATED WITH JEDEC DO-41 OUTLINE SHALL APPLY
 POLARITY DENOTED BY CATHODE BAND.
 LEAD DIAMETER NOT CONTROLLED WITHIN F DIMENSION DIMENSION.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.161	0.205	4.10	5.20
В	0.079	0.106	2.00	2.70
D	0.028	0.034	0.71	0.86
F		0.050		1.27
ĸ	1.000		25.40	

STYLE 1: PIN 1. CATHODE (POLARITY BAND) 2. ANODE

SWITCHMODE is a trademark of Semiconductor Components Industries, LLC.

ON Semiconductor and ()) are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and all vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death a Equilibutors tharmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death and personal injury or death and personal injury or death and succurs of the part. SCILLC is a figure of the part. SCILLC heads the second with such unintended or unauthorized use, even if such claim alleges that SCILLC areading the design or manufacture of the part. SCILLC is Equilable. associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA Phone: 303–675–2175 or 800–344–3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free USA/Canada Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910 Japan Customer Focus Center Phone: 81-3-5773-3850

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

MUR2100E/D